



- (51) **International Patent Classification:**
H01L 27/108 (2006.01) *H01L 21/205* (2006.01)
H01L 21/203 (2006.01)
- (21) **International Application Number:**
PCT/US2015/020501
- (22) **International Filing Date:**
13 March 2015 (13.03.2015)
- (25) **Filing Language:** English
- (26) **Publication Language:** English
- (30) **Priority Data:**
14/249,327 9 April 2014 (09.04.2014) US
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- (81) **Designated States** (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY,
BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM,
DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT,
HN, HR, HU, ID, IL, IN, IR, IS, JP, KE, KG, KN, KP, KR,
KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG,
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SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN,
TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.
- (84) **Designated States** (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ,
TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU,
TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE,
DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU,
LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK,
SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, KM, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) **Title:** CAPACITOR ASSEMBLIES FOR COUPLING RADIO FREQUENCY (RF) AND DIRECT CURRENT (DC) EN-
ERGY TO ONE OR MORE COMMON ELECTRODES

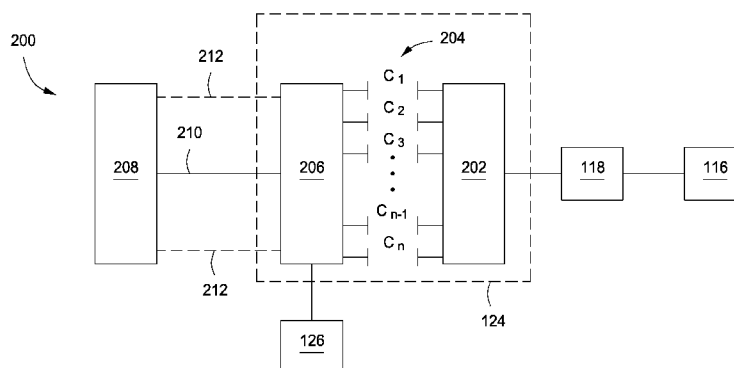


FIG. 2

(57) **Abstract:** Embodiments of a capacitor assembly for coupling radio frequency (RF) and direct current (DC) power to an electrode and substrate support incorporating same are provided herein. In some embodiments, the capacitor assembly includes a first conductive plate to receive RF power from an RF power source, the first conductive plate including a central bore; at least one capacitor coupled to the first conductive plate and surrounding the central bore; and a second conductive plate electrically coupled to the first conductive plate via the at least one capacitor, the second conductive plate including an input tap to receive DC power from a DC power source and at least one output tap to couple the RF and DC power to an electrode.

CAPACITOR ASSEMBLIES FOR COUPLING RADIO FREQUENCY (RF) AND DIRECT CURRENT (DC) ENERGY TO ONE OR MORE COMMON ELECTRODES

FIELD

[0001] Embodiments of the present disclosure generally relate to substrate processing equipment.

BACKGROUND

[0002] Formation of microelectronic devices on substrates often requires multiple layers of thin films which are deposited in a deposition chamber, such as, for example, a physical vapor deposition (PVD) chamber, an atomic layer deposition (ALD) chamber, a chemical vapor deposition (CVD) chamber, etc. An electrostatic chuck is often used to electrostatically retain a substrate on a substrate support during the deposition process. Direct current (DC) power, from a DC power supply, is typically provided to an electrode in the chuck to electrostatically retain the substrate on the chuck.

[0003] In addition, radio frequency (RF) energy is also often supplied to an electrode in the substrate support to control the energy of incoming ions travelling toward the substrate. In some cases, the DC and RF energy are provided to the same electrode. For example, high current DC power is delivered to one or more electrodes in the electrostatic chuck while isolating the RF power from the DC current. Vacuum-style capacitors have been used to isolate RF power from the DC current. However, the inventors have noted that vacuum-style capacitors are large (e.g., about 2-3 inches) and use up valuable space. Furthermore, in order to meet increased power demands in an electrostatic chuck, even larger capacitors would be necessary, hence further using up valuable space. Other conventional designs include in-line arrays of capacitors. However, the inventors believe that the in-line array is also inefficient because additional capacitors must be added to meet added power requirements of the electrostatic chuck.

[0004] Therefore, the inventors have provided embodiments of improved capacitor assemblies for coupling RF and DC energy to an electrode.

SUMMARY

[0005] Embodiments of capacitor assemblies for coupling radio frequency (RF) and direct current (DC) energy to an electrode and substrate supports incorporating the capacitor assembly are provided herein. In some embodiments, a capacitor assembly includes a first conductive plate to receive RF power from an RF power source, the first conductive plate including a central bore; at least one capacitor coupled to the first conductive plate and surrounding the central bore; and a second conductive plate electrically coupled to the first conductive plate via the at least one capacitor, the second conductive plate including an input tap to receive DC power from a DC power source and at least one output tap to couple the RF and DC power to an electrode.

[0006] In some embodiments, a capacitor assembly for coupling RF and DC power to an electrode includes a circular conductive plate to receive RF power from an RF power source, the circular conductive plate including a central bore; a plurality of capacitors coupled to the first conductive plate and radially disposed about the central bore; and a second conductive plate electrically coupled to the circular conductive plate via the plurality of capacitors, the second conductive plate including an input tap to receive DC power from a DC power source and at least one output tap to couple the RF and DC power to an electrode.

[0007] In some embodiments, a substrate support assembly includes a substrate support including at least one chucking electrode; an direct current (DC) power source; a radio frequency (RF) power source; and at least one capacitor assembly electrically coupled to the at least one chucking electrode. The at least one capacitor assembly includes a first conductive plate to receive RF power from an RF power source, the first conductive plate including a central bore; at least one capacitor coupled to the first conductive plate and surrounding the central bore; and a second conductive plate electrically coupled to the first conductive plate via the at least one capacitor, the second conductive plate including an input tap to receive DC power from a DC power source and at least one output tap to couple the RF and DC power to an electrode.

[0008] Other and further embodiments of the present disclosure are described below.

BRIEF DESCRIPTION OF THE DRAWINGS

[0009] Embodiments of the present disclosure, briefly summarized above and discussed in greater detail below, can be understood by reference to the illustrative embodiments of the disclosure depicted in the appended drawings. However, the appended drawings illustrate only typical embodiments of the disclosure and are therefore not to be considered limiting of scope, for the disclosure may admit to other equally effective embodiments.

[0010] Figure 1 depicts a simplified schematic view of a process chamber suitable for use with the inventive capacitor assembly in accordance with some embodiments of the present disclosure.

[0011] Figure 2 depicts a schematic of a capacitor assembly in accordance with some embodiments of the present disclosure.

[0012] Figure 3 depicts an isometric view of a capacitor assembly in accordance with some embodiments of the present disclosure.

[0013] Figure 3A depicts a side cross-sectional view of a capacitor assembly in accordance with some embodiments of the present disclosure.

[0014] Figure 4 depicts a side cross-sectional view of a capacitor assembly in accordance with some embodiments of the present disclosure.

[0015] Figure 5 depicts a schematic of a capacitor assembly in accordance with some embodiments of the present disclosure.

[0016] To facilitate understanding, identical reference numerals have been used, where possible, to designate identical elements that are common to the figures. The figures are not drawn to scale and may be simplified for clarity. Elements and features of one embodiment may be beneficially incorporated in other embodiments without further recitation.

DETAILED DESCRIPTION

[0017] Embodiments of capacitor assemblies and substrate supports incorporating capacitor assemblies are provided herein. Embodiments of the inventive capacitor assembly may advantageously prevent direct current (DC) from interfering with a radio frequency (RF) power source when both DC and RF power are provided to a common electrode. Embodiments of the inventive capacitor assembly may advantageously be easily retrofitted to existing substrate supports, thus avoiding unnecessary and potentially costly modification of the existing substrate supports.

[0018] Figure 1 depicts a simplified schematic side view of an illustrative substrate processing chamber suitable for use with capacitor assemblies in accordance with embodiments of the present disclosure. The process chamber 100 may be any type of process chamber suitable to process substrates, for example, such as a physical vapor deposition (PVD) chamber, an atomic layer deposition (ALD) chamber, a chemical vapor deposition (CVD) chamber, or the like. Exemplary process chambers may include process chambers available from Applied Materials, Inc. of Santa Clara, California, as well as process chambers available from other manufacturers.

[0019] As described in Figure 1, the process chamber 100 may comprise a chamber body 102, a lid assembly 104 including a target 106 (or showerhead) secured to the lid assembly 104, and a substrate support 108 for retaining a substrate 110 in a position opposite the target 106. Although Figure 1 depicts a target 106, alternatively a showerhead or other processing component may replace and be disposed in the location of the target 106 depending upon the chamber configuration. The inventive capacitor assembly may generally be used in any process chamber where RF and DC energy is provided to a common electrode.

[0020] The process chamber 100 has an inner volume that includes a processing volume 105. The processing volume 105 may be defined, for example, between the substrate support 108 and the target 106 (or showerhead or lid of the chamber). The substrate support 108 includes an electrostatic chuck to retain the substrate 110 on the substrate support. Suitable substrates 110 include round substrates, such as

200mm, 300mm, 450mm, or other diameter semiconductor wafers, or rectangular substrates, such as glass panels or the like.

[0021] The substrate support 108 includes an electrode 114 that is coupled to one or more RF power sources and a DC power source. Thus, the electrode 114 is both an RF bias electrode and a chucking electrode. The electrode 114 is coupled to one or more RF power sources (one RF power source 116 shown) through one or more respective matching networks (matching network 118 shown). The RF power source 116 may provide either continuous or pulsed power at a frequency suitable for use in the process chamber, for example, dependent upon chamber configuration, substrate composition, and particular processes to be performed. RF power may be provided at a suitable magnitude for the process being performed.

[0022] The electrode 114 is further coupled to a DC power source 126 to supply DC power to the electrode 114. The DC power source 126 may be any suitable DC power source as used to provide sufficient energy for the desired application, for example, to electrostatically clamp a substrate to the substrate support.

[0023] A capacitor assembly 124 is provided between the RF power source 116 and the electrode 114. If a matching network 118 is present, the capacitor assembly 124 is disposed between the matching network 118 and the electrode 114 as well. The DC power source 126 is coupled to the electrode 114 at a junction between the capacitor assembly 124 and the electrode 114. Although the following description is made with regard to an electrostatic chuck, the capacitor assembly 124 may be used in any application in which DC voltage needs to be blocked and RF is connected or matched.

[0024] In some embodiments, the substrate support 108 may be coupled to a lift mechanism 112 to control the position of the substrate support 108. The lift mechanism 112 may move the substrate support 108 between a lower position (as shown) suitable for transferring substrates into and out of the chamber and an upper position suitable for processing.

[0025] In some embodiments, one or more RF power sources (one RF power source 120 shown) may be coupled to the process chamber 100 to supply RF power to the target 106. For example, the RF power source 120 may be coupled to a lid

assembly 104 of the process chamber 100 via one or more respective match networks (one match network 122 shown).

[0026] Figure 2 depicts a schematic diagram of a capacitor assembly 200 in accordance with some embodiments of the present disclosure. The capacitor assembly 200 may be used as the capacitor assembly 124 discussed above with respect to Figure 1. The capacitor assembly 200 includes a first conductive plate 202, a second conductive plate 206, and a plurality of capacitors 204 disposed and electrically coupled between the first conductive plate 202 and the second conductive plate 206. The plurality of capacitors 204 may be electrically coupled the each of the first and second conductive plates in any suitable manner, such as by soldering, brazing, or the like.

[0027] The plurality of capacitors 204 are arranged in a circular array (as shown in an illustrative example in Figures 3-4). In some embodiments, the plurality of capacitors 204 are arranged in a circular array axisymmetrically with respect to a central axis of the circular array (as shown in the illustrative example of Figures 3-4). In some embodiments, about 9 capacitors are provided in the circular array. However, the number of capacitors is only limited by the size of the capacitor assembly 200 and that any number of capacitors (*i.e.*, one or more) may alternatively be used. Each of the plurality of capacitors 204 has substantially the same capacitance. The plurality of capacitors 204 may generally include any number of capacitors in any size depending on the frequency of the RF power and physical space limitations.

[0028] The first conductive plate 202 is coupled to the RF power source 116 (via the matching network 118, when present) to receive RF power from the RF power source 116. The second conductive plate 206 is electrically coupled to a load 208, for example via conductor 210. For example, the load 208 may be the electrode 114, described above with respect to Figure 1. In some embodiments, the second conductive plate 206 may be coupled to the load 208 at a plurality of locations, for example using additional conductors 212. In some embodiments, the conductor 210 and the additional conductors are substantially evenly spaced apart from each other

to advantageously receive and distribute an approximately equal portion of the RF power provided by the RF power source 116 to the load 208.

[0029] The DC power source 126 is also coupled to the load 208 at one or more locations. In some embodiments, the DC power source 126 is coupled to the second conductive plate 206 to receive DC power from the DC power source 126 such that the DC power source 126 is coupled to the load 208 via the conductor 210 and, if present, any additional conductors 212. In some embodiments, the DC power source 126 may be coupled to the load 208 via the additional conductors 212 or a separate conductor (not shown) coupling the DC power source 126 directly or indirectly to the load 208.

[0030] In operation, RF energy is provided by the RF power source 116 to the first conductive plate 202. The RF energy travels across the plurality of capacitors 204 to the second conductive plate 206. The radial arrangement of the plurality of capacitors advantageously provides more even distribution of RF power to each portion of the load as compared to conventional rectangular arrays, which have shown unsatisfactory distribution. The RF energy is coupled to the load 208 by the conductor 210 and any additional conductors 212. DC power is coupled to the load 208 by the conductor 210 (and any additional conductors 212), or via a separate conductor (not shown). In some embodiments, the DC power source 126 is coupled to the second conductive plate 206 and the DC power is coupled to the load 208 via the conductor 210 and any additional conductors 212.

[0031] Figure 3 depicts an isometric view of an illustrative capacitor assembly 300 in accordance with some embodiments of the present disclosure. The capacitor assembly 300 is illustrative of a particular configuration of the capacitor assembly 200 and is not meant to be limiting of the scope of the disclosure. The capacitor assembly 300 includes a first conductive plate 302 and a second conductive plate 304. A plurality of capacitors 306 are disposed between and electrically couple the first and second conductive plates 302, 304. The first and second conductive plates 302, 304 may be formed of any suitable conductive material. In some embodiments, the first and second conductive plates 302, 304 may be coated with a material having a resistance to tarnishing or oxidation, such as silver, gold, or other metals

whose impedance is not adversely affected by tarnishing. For example, in some embodiments, the first and second conductive plates 302, 304 are formed from copper and have a coating of silver.

[0032] As illustrated in Figure 3, the first conductive plate 302 may be circular or have some other symmetrical shape to promote a substantially uniform flow of RF energy to each of the plurality of capacitors 306. The first conductive plate 302 includes a feature for coupling the RF energy to the first conductive plate 302, such as a bore 308. In some embodiments, the feature may be centrally located in or on the first conductive plate 302. For example, as depicted in Figure 3, the bore 308 is centered on the first conductive plate 302. In some embodiments, the bore 308 may be threaded to receive a correspondingly threaded bolt.

[0033] A conductor coupled to the RF power source 116, such as an output from matching network 118, is coupled to the first conductive plate 302. For example, in some embodiments, a conductor may be bolted to the first conductive plate 302 via the bore 308. Figure 3A depicts a side cross sectional view of the capacitor assembly 300 in accordance with some embodiments of the present disclosure. In some embodiments, and as depicted in Figure 3A, a third conductive plate 316 may be coupled to an output from the matching network 118. The third conductive plate 316 may be coupled to the first conductive plate 302, for example using a bolt 318 threaded into the bore 308 of the first conductive plate 302. In some embodiments, the first conductive plate 302 may further comprise a groove 314 to receive an RF gasket 310 to enhance surface contact between the surface of the third conductive plate 316 and the facing surface of the first conductive plate 302, thus promoting enhanced flow of RF current to the first conductive plate 302. The RF gasket 310 may be formed of any conductive material with a metal coating whose impedance is not adversely affected by tarnishing. In some embodiments, the RF gasket 310 is formed of silver-plated copper.

[0034] Returning to Figure 3, the plurality of capacitors 306 may individually be any conventional capacitors suitable for the application, such as, for example, porcelain style ceramic capacitors, although other types of capacitors may also be used. In some embodiments, the plurality of capacitors are radially arranged about the bore

308 to ensure uniform delivery of RF power to the second conductive plate 304. The radial arrangement of the plurality of capacitors 306 further advantageously avoids areas of high temperature in the capacitor assembly 300 and reduces the overall size of the capacitor assembly 300. The size of the capacitors 306 are chosen to ensure a distance between the first and second conductive plates 302, 304 large enough to avoid arcing and ensure sufficient voltage isolation. In some embodiments, a tubular capacitor with the desired capacitance may alternatively be used instead of the plurality of capacitors 306.

[0035] The following description of the second conductive plate 304 is made with reference to Figures 3 and 4. Figure 4 depicts a side cross-sectional view of the capacitor assembly 300 showing the plurality of capacitors 306. In some embodiments, the second conductive plate 304 may include a bore 402. The bore 402 may be centered in the second conductive plate 304. In some embodiments, the second conductive plate 304 may include a pair of flanges 404. The flanges 404 may be disposed on generally opposing sides of the second conductive plate 304 proximate a first end 408 of the second conductive plate 304.

[0036] An input tap 412 may be provided in the second conductive plate 304. In some embodiments, the input tap 412 is formed in the first end 408 of the second conductive plate 304. In some embodiments, the input tap 412 is formed proximate the center of the first end 408. The input tap 412 may be coupled to a DC power source (e.g., DC power source 126) to receive DC power.

[0037] The second conductive plate 304 includes one or more output taps 312 to deliver power to the load (e.g., load 208 described above with respect to Figure 2). In embodiments where a plurality of output taps 312 are provided, the output taps 312 may be equidistantly spaced from each other. In embodiments where a plurality of output taps 312 are provided, the output taps 312 may be axisymmetrically arranged on the second conductive plate 304. The axis of symmetry of the output taps 312 may be the same as the axis of symmetry of the plurality of capacitors 306. In some embodiments, an output tap 312 is formed in each of the flanges 404 and in a second end 406 of the second conductive plate 304 opposite the first end 408.

[0038] The one or more output taps 312 may be electrically coupled to the load (e.g., the electrode 114). A symmetric arrangement of the output taps 312 about the second conductive plate 304 promotes a more uniform delivery of DC and RF power to the load. However, the output taps 312 may be formed anywhere on the second conductive plate 304. Each output tap 312 may be associated with a different load (e.g., a different electrode) or the same load (e.g., the same electrode). In some embodiments, a filter board (not shown) may be disposed between the second conductive plate 304 and the DC power source 126 to prevent RF energy from travelling to the DC power source 126.

[0039] Figure 4 illustratively depicts nine capacitors. However, any number of capacitors may be used to deliver the desired amount of power to the load. For example, the diameter of the first and second conductive plates 302, 304 may be larger (or smaller) to accommodate more (or fewer) capacitors to meet higher (or lower) power requirements. Alternatively or in combination, capacitors with different values may be used to meet specific frequency requirements.

[0040] Figure 5 depicts a schematic view of a capacitor assembly 500 in accordance with some embodiments of the present disclosure. In some embodiments, two or more capacitor assemblies, similar to capacitor assembly 200 or 300 as described above, may be stacked to increase the amount of power that can be handled by the assembly. In a stacked configuration, an intermediate conductive plate 502 (similar to the first conductive plate 302) is coupled to the first conductive plate 302 by a first plurality of capacitors 306 and coupled to the second conductive plate 304 by a second plurality of capacitors 506. In some embodiments, the intermediate conductive plate 502 may be directly coupled to a second intermediate conductive plate 504 (as depicted in phantom) and the second intermediate conductive plate 504 is coupled to the second conductive plate 304 by the second plurality of capacitors 506. Providing the second intermediate conductive plate 504 advantageously facilitates ease of construction and modularity of assembly.

[0041] Such a configuration would be desirable, for example, if the amount of voltage necessary to provide to the load (e.g., the electrode 114) is very large. In

such cases where the voltage is very large, the distance between the second conductive plate 304, which receives DC power, and the first conductive plate 302, which receives RF power from the matching network 118, must be large enough to isolate the RF power from the DC current. Stacking the capacitor assemblies 300 would achieve the necessary voltage isolation. Alternatively, a longer capacitor or stacked capacitors may be used to increase the distance between the first conductive plate 302 and the second conductive plate 304.

[0042] While the foregoing is directed to embodiments of the present disclosure, other and further embodiments may be devised without departing from the basic scope thereof.

Claims:

1. A capacitor assembly for coupling radio frequency (RF) and direct current (DC) power to an electrode, comprising:
 - a first conductive plate to receive RF power from an RF power source, the first conductive plate including a central bore;
 - at least one capacitor coupled to the first conductive plate and surrounding the central bore; and
 - a second conductive plate electrically coupled to the first conductive plate via the at least one capacitor, the second conductive plate including an input tap to receive DC power from a DC power source and at least one output tap to couple the RF and DC power to an electrode.
2. The capacitor assembly of claim 1, wherein the first conductive plate is circular.
3. The capacitor assembly of any of claims 1 or 2, wherein the at least one capacitor is a tubular capacitor.
4. The capacitor assembly of any of claims 1 or 2, wherein the at least one capacitor is a plurality of capacitors radially disposed about the central bore.
5. The capacitor assembly of claim 4, further comprising:
 - an intermediate conductive plate; and
 - a second plurality of capacitors coupled to the intermediate conductive plate, wherein the plurality of capacitors is disposed between the first conductive plate and the intermediate conductive plate, and
 - wherein the second plurality of capacitors is disposed between the intermediate conductive plate and the second conductive plate.
6. The capacitor assembly of any of claims 1 or 2, further comprising:
 - a third conductive plate to couple the RF power to the first conductive plate;

wherein the central bore of the first conductive plate is threaded to receive a correspondingly threaded bolt to couple the third conductive plate to the first conductive plate.

7. The capacitor assembly of claim 6, wherein the first conductive plate comprises a groove containing a gasket to increase surface contact between the third conductive plate and the first conductive plate.

8. The capacitor assembly of any of claims 1 or 2, wherein the at least one output tap comprises a plurality of output taps.

9. The capacitor assembly of claim 8, wherein each of the plurality of output taps is coupled to a respective electrode.

10. A substrate support assembly, comprising:
a substrate support including at least one electrode; and
at least one capacitor assembly electrically coupled to the at least one chucking electrode, the at least one capacitor assembly comprising the capacitor assembly of any of claims 1 to 9.

11. The substrate support assembly of claim 10, further comprising:
a direct current (DC) power source coupled to the electrode.

12. The substrate support assembly of claim 11, wherein the DC power source is coupled to electrode via the input tap of the second conductive plate.

13. The substrate support assembly of claim 10, further comprising:
a radio frequency (RF) power source coupled to the first conductive plate.

14. The substrate support assembly of claim 13, further comprising:
an RF matching network disposed between the capacitor assembly and the RF power source.

15. The substrate support assembly of any of claims 10 to 14, wherein the substrate support assembly is an electrostatic chuck.

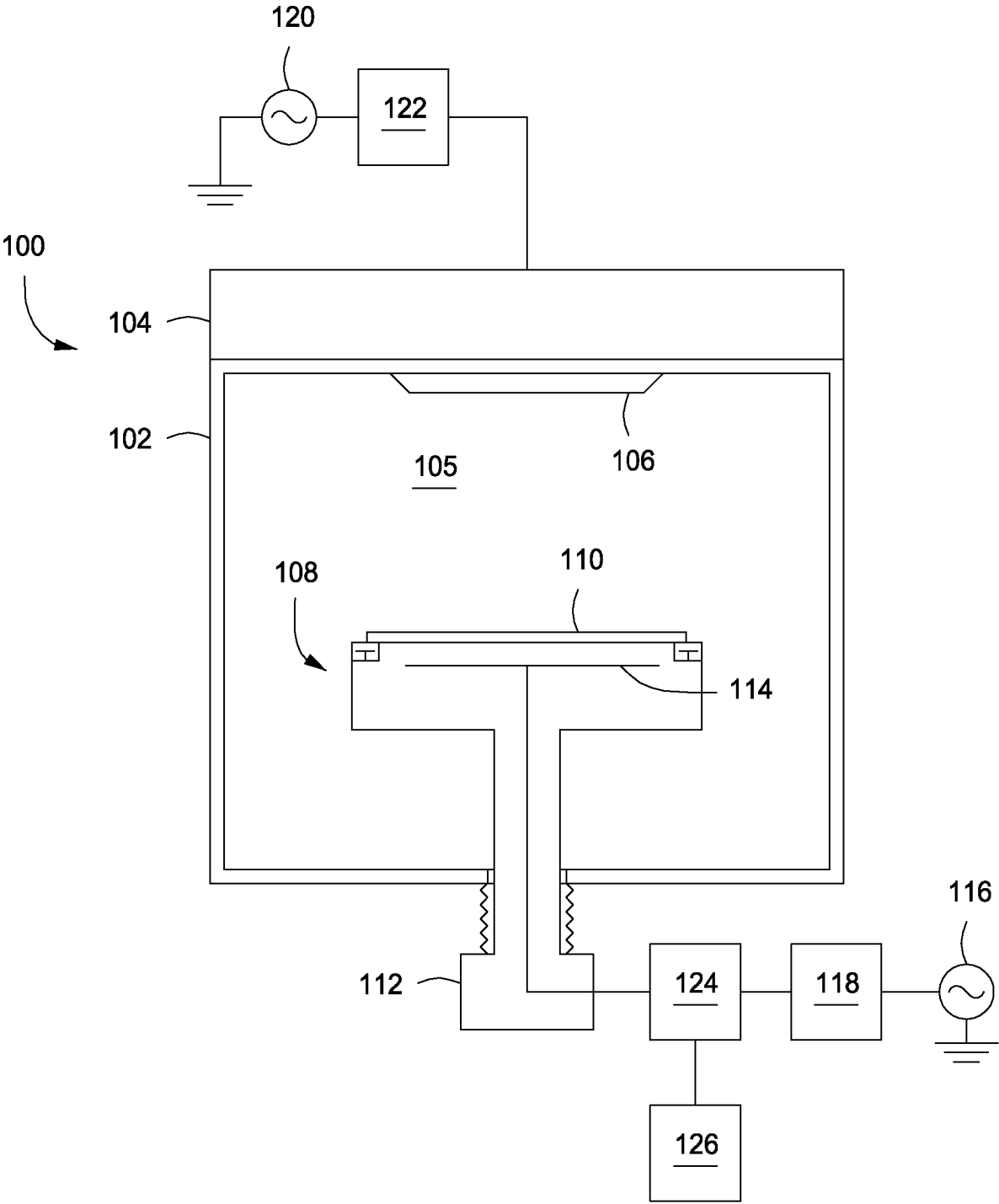


FIG. 1

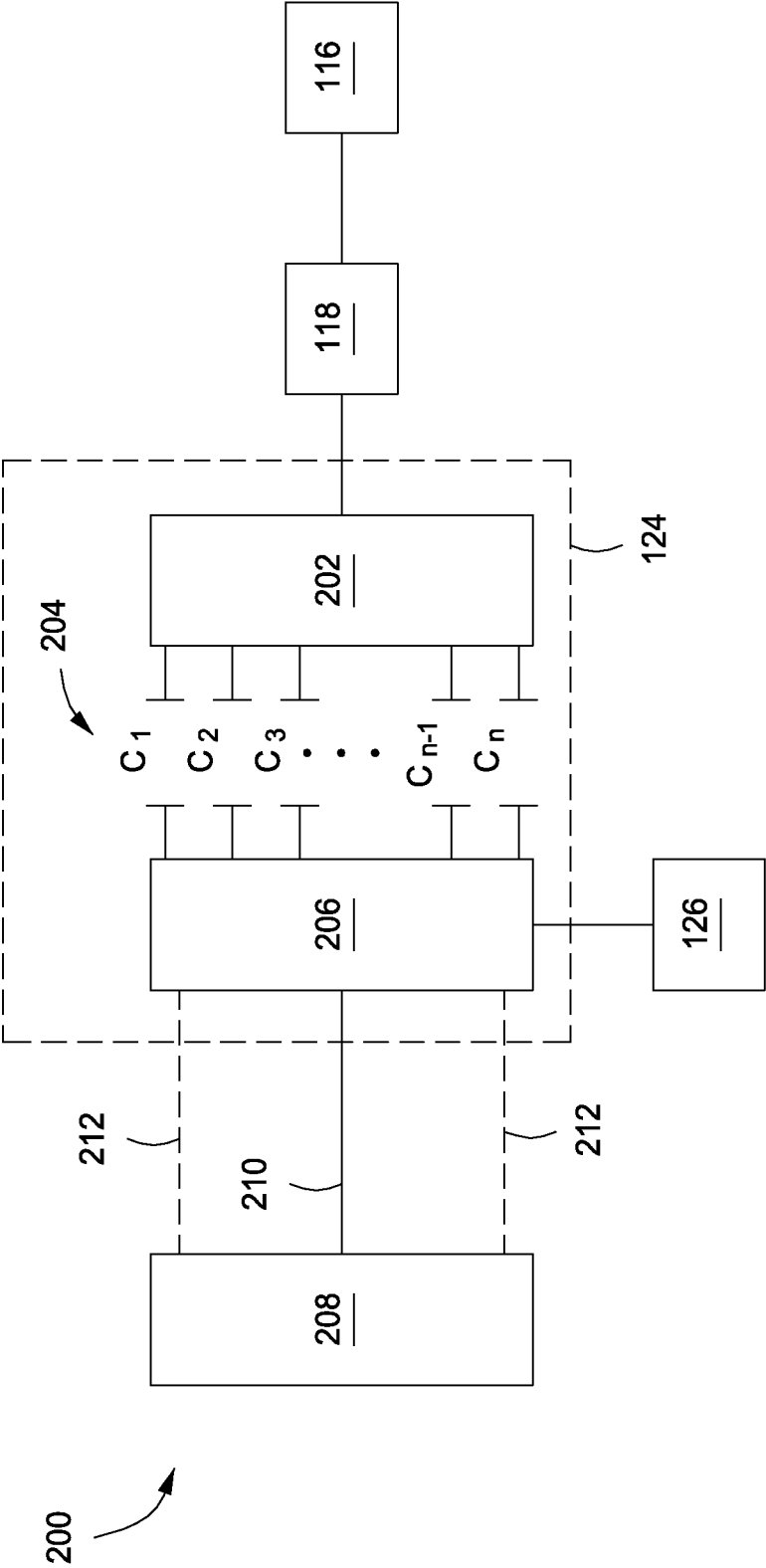


FIG. 2

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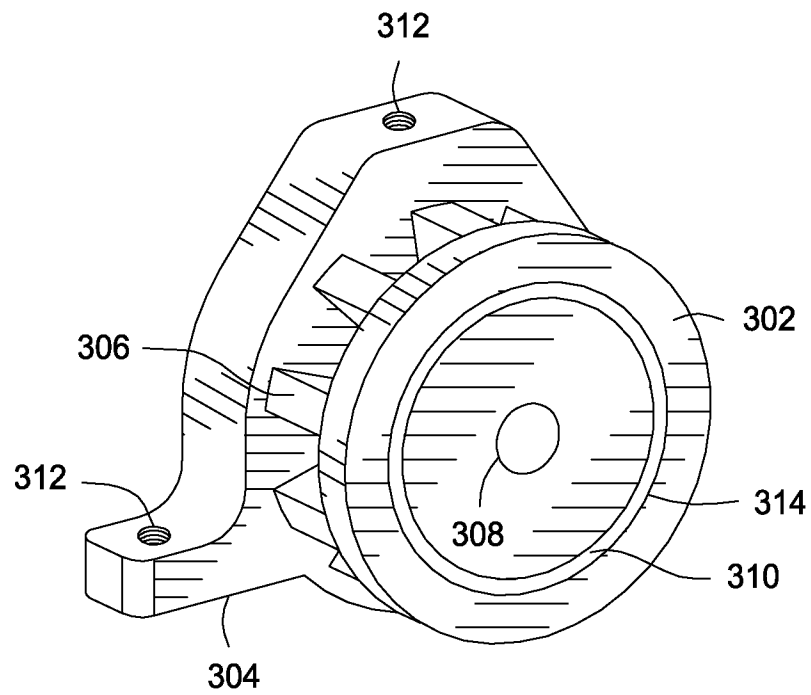
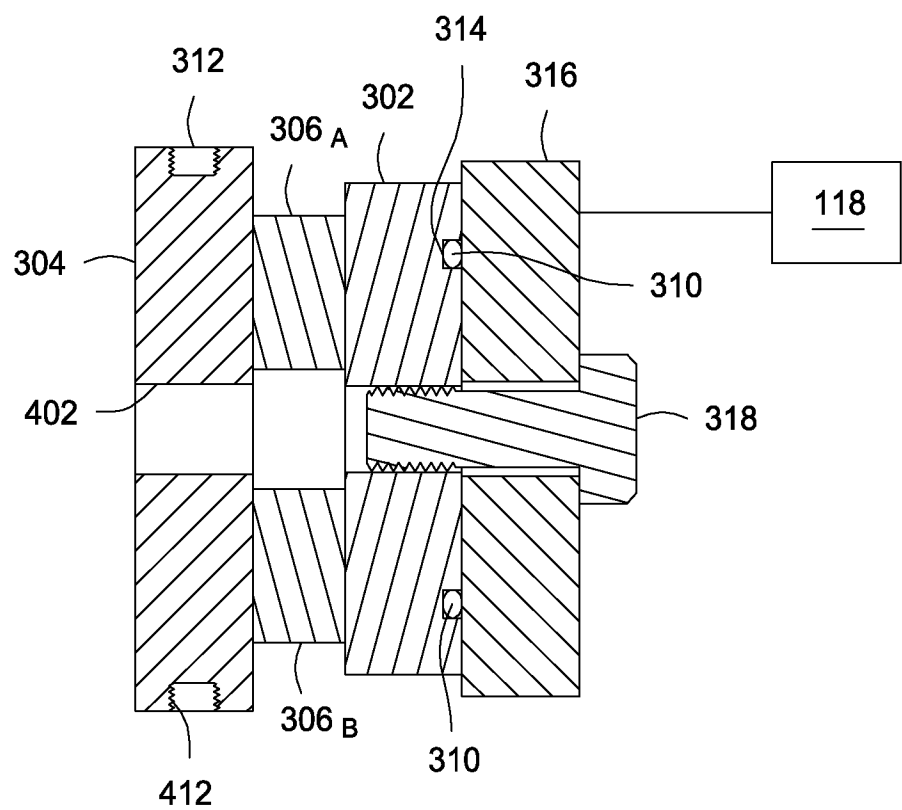


FIG. 3

FIG. 3A



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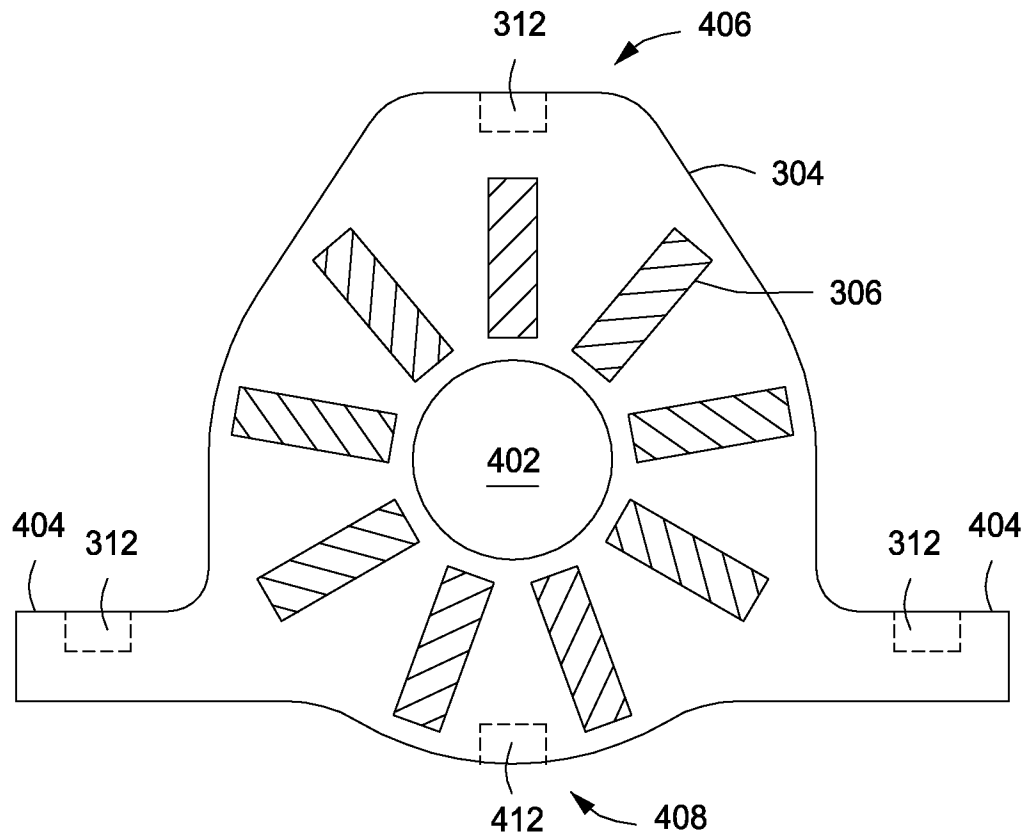


FIG. 4

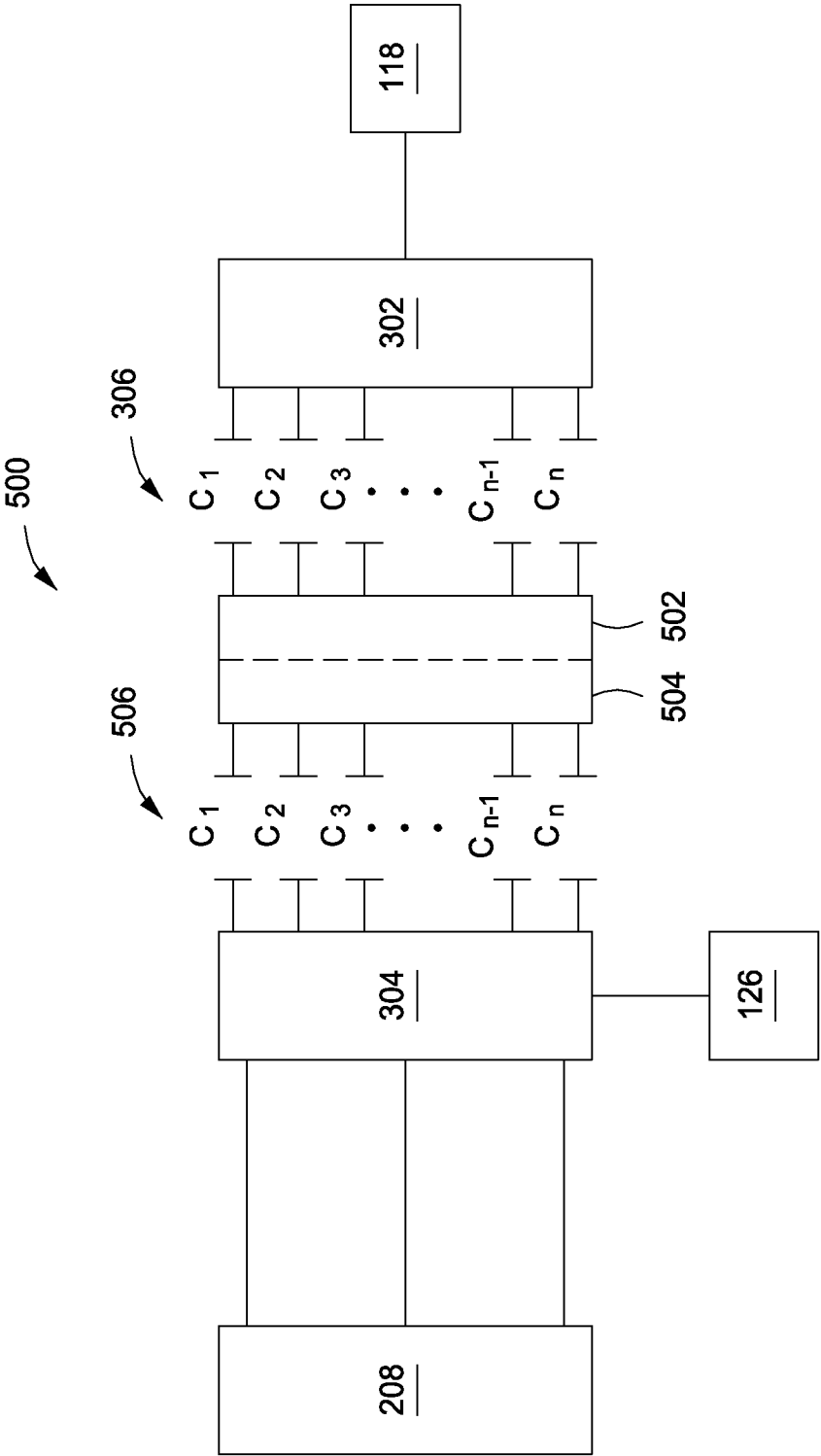


FIG. 5

INTERNATIONAL SEARCH REPORT

International application No.
PCT/US2015/020501**A. CLASSIFICATION OF SUBJECT MATTER****H01L 27/108(2006.01)i, H01L 21/203(2006.01)i, H01L 21/205(2006.01)i**

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

H01L 27/108; C23C 16/503; H01L 21/3065; H01L 21/302; H01L 21/68; C23C 16/509; H01L 21/461; B23K 10/00; H01L 21/203; H01L 21/205

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

Korean utility models and applications for utility models

Japanese utility models and applications for utility models

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

eKOMPASS(KIPO internal) & Keywords: capacitor, coupling, radio frequency, direct current

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
A	US 6431112 B1 (EDWARD L. SILL et al.) 13 August 2002 See abstract, column 5, line 6 - column 10, line 6 and figures 1-3.	1-15
A	US 2010-0136793 A1 (ZHIGANG CHEN et al.) 03 June 2010 See abstract, paragraphs [0024]-[0025] and figure 1A.	1-15
A	US 5670066 A (MICHAEL S. BARNES et al.) 23 September 1997 See abstract, column 3, line 26 - column 6, line 3 and figures 1-2.	1-15
A	US 2002-0042204 A1 (HISATAKA HAYASHI et al.) 11 April 2002 See abstract, paragraphs [0030]-[0058] and figures 3-6.	1-15
A	WO 00-41229 A1 (TOKYO ELECTRON LIMITED) 13 July 2000 See abstract, pages 7-11 and figure 1.	1-15



Further documents are listed in the continuation of Box C.



See patent family annex.

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Date of the actual completion of the international search

24 June 2015 (24.06.2015)

Date of mailing of the international search report

24 June 2015 (24.06.2015)

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INTERNATIONAL SEARCH REPORT

Information on patent family members

International application No.

PCT/US2015/020501

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